Journal of Low Power ELECTRONICS

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Aims and Scope:

The electronic systems that can operate with a very low power are of great interest in modern hi-tech industries. The growing research activity in the field of low power electronics requires a forum for rapid dissemination of important results and advancing our knowledge of the science: ***Journal of Low Power Electronics*** (JOLPE) is that international forum which offers vital new information across a broad range of topics in this field. The journal covers all experimental and theoretical aspects in the field of low power electronics.

Research Topics Covered (but not limited to):

Broadly speaking all aspects of low-power electronics are covered. The keywords include low-power high performance electronic systems, design and tools, embedded and real-time low power systems, architectures for low power systems, devices and components, low power scheduling algorithms, low power synthesis, variability-aware low power design, low power design under reliability constraints, asynchronous design, low power analog design, low power memory design, wireless sensor networks, power management design for Network-on-Chip applications, thermal analysis and processing, simulation of low power electronic systems, tools and techniques for power estimation and management, power-aware testing, test and reliability issues in the presence of leakage, challenges of ultra low-power design on test and reliability, wireless communications and signal processing, computer systems, portable communication and multimedia devices, analog/mixed-signal electronics, digital electronics, low-voltage analogs, RF devices and circuits, low-voltage high-speed CMOS and BiCMOS, power dissipation and energy recovery in CMOS circuits, low power digital circuits, bus encoding for low-power, low power analog devices and techniques, low-power ADC, low-power image sensing devices, leakage reduction, algorithmic transformations and caching, low-power motion analysis in videos, low-power audios, low-power mapping for logics, power reduction through energy reuse, rapid thermal processing, low-voltage power supplies, low-power biomedical systems, converters, tools and techniques for power estimation and management, military and aerospace applications, space-based satellites, portable communication and multimedia devices, laptops, cell phones, pagers, palmtops, video recorders, pacemakers, portable instruments, low power medical devices, biomedical imaging, low-power signal processing and other low-power related applications, etc.

Manuscript Submission:

You are kindly requested to submit original research (fundamental or applied research aspects) articles. Please submit your manuscript to the Editor-in-Chief. When preparing your manuscript, please follow the journal style guidance and make your paper "ready for publication" (all details, notes, appendix, figures, images, etc. must be provided in the submitted version of the manuscript). Instructions for authors are available at ***www.aspbs.com/jolpe***.

Deadline:

The deadline for submitting your manuscript for ***JOLPE Vol. 9, N° 2*** *is* ***February 15, 2013****. Notification of acceptance will be sent on* ***May 2013****. Accepted papers will be published in* ***August 2013.***

Authors are kindly advised to read ***Journal of Low Power Electronics*** policy and also the uniform requirements for manuscripts submission. Authors are encouraged to submit high quality original research work that has not been published or nor under consideration by other journals or conference proceedings elsewhere. Authors should submit manuscript electronically as a PDF file to the **Editor-in-Chief** Dr. Patrick GIRARD at girard@lirmm.fr

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